connecting layer consists of the iron/nitrogen layer bearing the chemical designation Fe_2N or Fe_3N.

IN THE CLAIMS:

Please amend claims 12-14, 19, 20, 23, 32, 33, 36, 41, and 45-47 as follows **(a marked-up version of the amended claims is attached hereto)**:

12. (Amended) Synchronizing device for a shift transmission, comprising at least one outer and one inner synchro ring and at least one intermediate ring, the synchro rings and the intermediate ring in each case having conical surfaces, via which they are connected at least indirectly to one another, and at least one of the synchro rings and the intermediate ring including a metallic basic material, wherein at least one of the synchro rings and the intermediate ring include the metallic basic material which is nitride-hardened in such a way that, by process parameters being set during nitride-hardening, one of a non-metallic γ'-connecting layer and a non-metallic ε-connecting layer is formed on a conical surface of at least one of the synchro rings and the intermediate ring.

13. (Amended) Synchronizing device according to Claim 12, wherein a γ'-connecting layer is formed which includes Fe_4N.

14. (Amended) Synchronizing device according to Claim 12, wherein a ε-connecting layer is formed which includes Fe_2N or Fe_3N.

19. (Amended) Synchronizing device according to Claim 12, wherein nitriding depth is 200 to 800 μm.

20. (Amended) Synchronizing device according to Claim 12, wherein the γ'-connecting layer and the ε-connecting layer is 1 to 20 μm thick.

23. (Amended) Synchronizing device according to Claim 13, wherein a ε-connecting layer is formed which includes Fe_2N or Fe_3N.

32. (Amended) Synchronizing device according to Claim 13, wherein nitriding depth is 200 to 800 μm.

33. (Amended) Synchronizing device according to Claim 14, wherein nitriding depth is 200 to 800 μm.

36. (Amended) A synchronizing device assembly according to Claim 34, wherein said first synchro ring is nitride hardened to form a non-metallic ε-connecting layers of Fe_2N or Fe_3N on said first friction surface.

41. (Amended) A synchronizing device assembly according to Claim 34, wherein nitriding depth on the first synchronizing is between 200 and 800 μm.

45. (Amended) A method according to Claim 44, further comprising nitride hardening said first synchro ring to form a non-metallic γ'-connecting layers of Fe_4N on said first friction surface.

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46. (Amended) A method according to Claim 44, further comprising nitride hardening said first synchro ring to form a non-metallic ε-connecting layers of Fe_2N or Fe_3N on said first friction surface.

47. (Amended) A method according to Claim 44, further comprising plasma-nitride-hardening said first synchro ring.

Please add the following new claim:

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48. (New) Synchronizing device according to Claim 20, wherein the γ'-connecting layer and the ε-connecting layer are approximately 10 μm thick.

(Applicant's Remarks are set forth hereinbelow, starting on the following page.)